

NB4N855S

3.3 V, 1.5 Gb/s Dual AnyLevel™ to LVDS Receiver/Driver/Buffer/Translator

Description

NB4N855S is a clock or data Receiver/Driver/Buffer/Translator capable of translating AnyLevel input signal (LVPECL, CML, HSTL, LVDS, or LVTTL/LVCMOS) to LVDS. Depending on the distance, noise immunity of the system design, and transmission line media, this device will receive, drive or translate data or clock signals up to 1.5 Gb/s or 1.0 GHz, respectively. This device is pin-for-pin plug in compatible to the SY55855V in a 3.3 V applications.

The NB4N855S has a wide input common mode range of $GND + 50\text{ mV}$ to $V_{CC} - 50\text{ mV}$. This feature is ideal for translating differential or single-ended data or clock signals to 350 mV typical LVDS output levels.

The device is offered in a small 10 lead MSOP package. NB4N855S is targeted for data, wireless and telecom applications as well as high speed logic interface where jitter and package size are main requirements.

Application notes, models, and support documentation are available at www.onsemi.com.

Features

- Guaranteed Input Clock Frequency up to 1.0 GHz
- Guaranteed Input Data Rate up to 1.5 Gb/s
- 490 ps Maximum Propagation Delay
- 1.0 ps Maximum RMS Jitter
- 180 ps Maximum Rise/Fall Times
- Single Power Supply; $V_{CC} = 3.3\text{ V} \pm 10\%$
- Temperature Compensated TIA/EIA-644 Compliant LVDS Outputs
- $GND + 50\text{ mV}$ to $V_{CC} - 50\text{ mV}$ V_{CMR} Range
- Pb-Free Package is Available

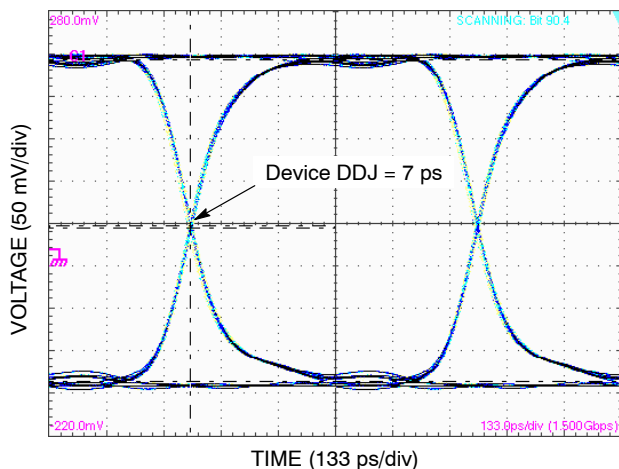
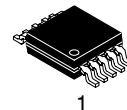


Figure 1. Typical Output Waveform at 1.5 Gb/s with K28.5 ($V_{INPP} = 100\text{ mV}$, Input Signal DDJ = 24 ps)



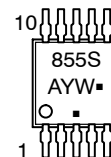
ON Semiconductor®

<http://onsemi.com>



Micro-10
M SUFFIX
CASE 846B

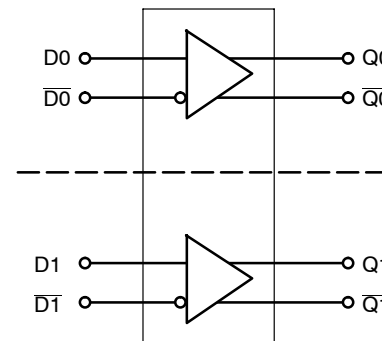
MARKING DIAGRAM*



- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

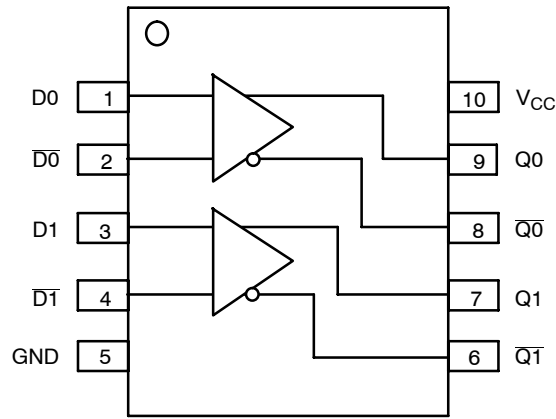


Functional Block Diagram

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

NB4N855S



**Figure 2. Pin Configuration and Block Diagram
(Top View)**

Table 1. PIN DESCRIPTION

Pin	Name	I/O	Description
1	D0	LVPECL, CML, LVCMOS, LVTTTL, LVDS	Noninverted Differential Clock/Data D0 Input.
2	$\overline{D0}$	LVPECL, CML, LVCMOS, LVTTTL, LVDS	Inverted Differential Clock/Data $\overline{D0}$ Input.
3	D1	LVPECL, CML, LVDS LVCMOS, LVTTTL	Noninverted Differential Clock/Data D1 Input.
4	$\overline{D1}$	LVPECL, CML, LVDS LVCMOS LVTTTL	Inverted Differential Clock/Data $\overline{D1}$ Input.
5	GND	-	Ground. 0 V.
6	$\overline{Q1}$	LVDS Output	Inverted $\overline{Q1}$ output. Typically loaded with 100 Ω receiver termination resistor across differential pair.
7	Q1	LVDS Output	Noninverted Q1 output. Typically loaded with 100 Ω receiver termination resistor across differential pair.
8	$\overline{Q0}$	LVDS Output	Inverted $\overline{Q0}$ output. Typically loaded with 100 Ω receiver termination resistor across differential pair.
9	Q0	LVDS Output	Noninverted Q0 output. Typically loaded with 100 Ω receiver termination resistor across differential pair.
10	V _{CC}	-	Positive Supply Voltage.

NB4N855S

Table 2. ATTRIBUTES

Characteristics		Value	
Moisture Sensitivity (Note 1)		Pb Pkg	Pb-Free Pkg
Micro-10		Level 1	Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
ESD Protection	Human Body Model Machine Model Charged Device Model	> 2 kV > 200 V > 1 kV	
Transistor Count		281	
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test			

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	GND = 0 V		3.8	V
V_I	Positive Input	GND = 0 V	$V_I = V_{CC}$	3.8	V
I_{IN}	Input Current Through R_T (50 Ω Resistor)	Static Surge		35 70	mA mA
I_{OSC}	Output Short Circuit Current Line-to-Line (Q to \bar{Q}) Line-to-End (Q or \bar{Q} to GND)	Q or \bar{Q} to GND Q to \bar{Q}	Continuous Continuous	12 24	mA
T_A	Operating Temperature Range	Micro-10		-40 to +85	$^{\circ}$ C
T_{stg}	Storage Temperature Range			-65 to +150	$^{\circ}$ C
θ_{JA}	Thermal Resistance (Junction-to-Ambient) (Note 2)	0 lfpm 500 lfpm	Micro-10 Micro-10	177 132	$^{\circ}$ C/W $^{\circ}$ C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	1S2P (Note 4)	Micro-10	40	$^{\circ}$ C/W
T_{sol}	Wave Solder	Pb Pb-Free	<3 Sec @ 248 $^{\circ}$ C <3 Sec @ 260 $^{\circ}$ C	265 265	$^{\circ}$ C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

2. JEDEC standard multilayer board – 1S2P (1 signal, 2 power).

NB4N855S

Table 4. DC CHARACTERISTICS, CLOCK INPUTS, LVDS OUTPUTS $V_{CC} = 3.0\text{ V to }3.6\text{ V}$, $GND = 0\text{ V}$, $T_A = -40^\circ\text{C to }+85^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Unit
I_{CC}	Power Supply Current (Note 3)		40	53	mA

DIFFERENTIAL INPUTS DRIVEN SINGLE-ENDED (Figures 10 and 12)

V_{th}	Input Threshold Reference Voltage Range (Note 4)	GND +100		$V_{CC} - 100$	mV
V_{IH}	Single-ended Input HIGH Voltage	$V_{th} + 100$		V_{CC}	mV
V_{IL}	Single-ended Input LOW Voltage	GND		$V_{th} - 100$	mV

DIFFERENTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11 and 13)

V_{IHD}	Differential Input HIGH Voltage	100		V_{CC}	mV
V_{ILD}	Differential Input LOW Voltage	GND		$V_{CC} - 100$	mV
V_{CMR}	Input Common Mode Range (Differential Configuration)	GND + 50		$V_{CC} - 50$	mV
V_{ID}	Differential Input Voltage ($V_{IHD} - V_{ILD}$)	100		V_{CC}	mV

LVDS OUTPUTS (Note 5)

V_{OD}	Differential Output Voltage	250		450	mV
ΔV_{OD}	Change in Magnitude of V_{OD} for Complementary Output States (Note 6)	0	1.0	25	mV
V_{OS}	Offset Voltage (Figure 9)	1125		1375	mV
ΔV_{OS}	Change in Magnitude of V_{OS} for Complementary Output States (Note 6)	0	1.0	25	mV
V_{OH}	Output HIGH Voltage (Note 7)		1425	1600	mV
V_{OL}	Output LOW Voltage (Note 8)	900	1075		mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- Dx/\overline{Dx} at the DC level within V_{CMR} and output pins loaded with $R_L = 100\ \Omega$ across differential.
- V_{th} is applied to the complementary input when operating in single-ended mode.
- LVDS outputs require $100\ \Omega$ receiver termination resistor between differential pair. See Figure 8.
- Parameter guaranteed by design verification not tested in production.
- $V_{OHmax} = V_{OSmax} + \frac{1}{2} V_{ODmax}$.
- $V_{OLmax} = V_{OSmin} - \frac{1}{2} V_{ODmax}$.

NB4N855S

Table 5. AC CHARACTERISTICS $V_{CC} = 3.0\text{ V to }3.6\text{ V}$, $GND = 0\text{ V}$; (Note 9)

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OUTPP}	Output Voltage Amplitude (@ $V_{INPPMIN}$) $f_{in} \leq 1.0\text{ GHz}$ (Figure 3) $f_{in} = 1.5\text{ GHz}$	230 200	350 300		230 200	350 300		230 200	350 300		mV
f_{DATA}	Maximum Operating Data Rate	1.5	2.5		1.5	2.5		1.5	2.5		Gb/s
t_{PLH} , t_{PHL}	Differential Input to Differential Output Propagation Delay	330	410	490	330	410	490	330	410	490	ps
t_{SKEW}	Duty Cycle Skew (Note 10) Within -Device Skew (Note 11) Device to Device Skew (Note 12)		8 10 20	45 35 100		8 10 20	45 35 100		8 10 20	45 35 100	ps
t_{JITTER}	RMS Random Clock Jitter (Note 13) $f_{in} = 1.0\text{ GHz}$ $f_{in} = 1.5\text{ GHz}$ Deterministic Jitter (Note 14) $f_{DATA} = 622\text{ Mb/s}$ $f_{DATA} = 1.5\text{ Gb/s}$ $f_{DATA} = 2.488\text{ Gb/s}$ Crosstalk Induced Jitter (Note 15)		0.5 0.5 6 7 10 20	1 1 15 20 25 40		0.5 0.5 6 7 10 20	1 1 15 20 25 40		0.5 0.5 6 7 10 20	1 1 15 20 25 40	ps
V_{INPP}	Input Voltage Swing/Sensitivity (Differential Configuration) (Note 16)	100		$V_{CC}-GND$	100		$V_{CC}-GND$	100		$V_{CC}-GND$	mV
t_r t_f	Output Rise/Fall Times @ 250 MHz (20% - 80%) Q, \bar{Q}	50	110	180	50	110	180	50	110	180	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

9. Measured by forcing $V_{INPPMIN}$ with 50% duty cycle clock source and $V_{CC} - 1400\text{ mV}$ offset. All loading with an external $R_L = 100\ \Omega$ across "D" and "D" of the receiver. Input edge rates 150 ps (20%-80%).
10. See Figure 7 differential measurement of $t_{skew} = |t_{PLH} - t_{PHL}|$ for a nominal 50% differential clock input waveform @ 250 MHz.
11. The worst case condition between $Q0/\bar{Q}0$ and $Q1/\bar{Q}1$ from either $D0/\bar{D}0$ or $D1/\bar{D}1$, when both outputs have the same transition.
12. Skew is measured between outputs under identical transition @ 250 MHz.
13. RMS jitter with 50% Duty Cycle clock signal.
14. Deterministic jitter with input NRZ data at PRBS $2^{23}-1$ and K28.5.
15. Crosstalk Induced Jitter is the additive Deterministic jitter to channel one with channel two active both running at 622 Gb/s PRBS $2^{23}-1$ as an asynchronous signals.
16. Input voltage swing is a single-ended measurement operating in differential mode.

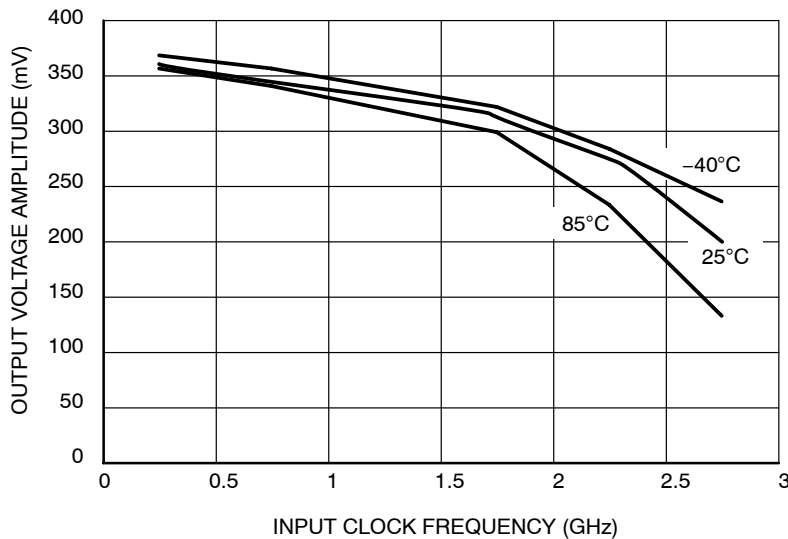
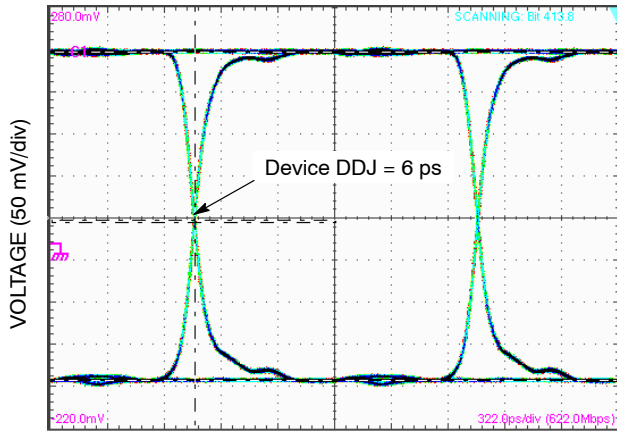
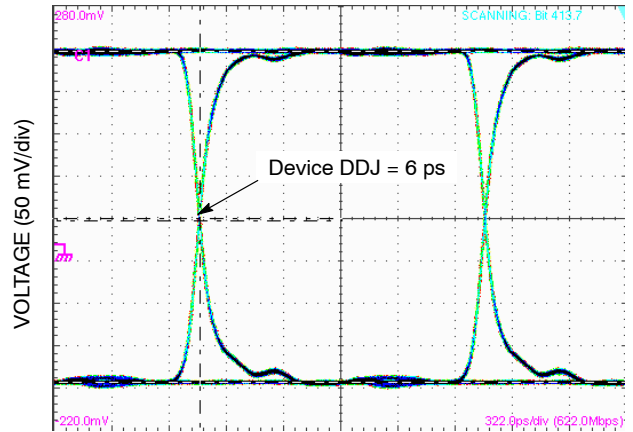


Figure 3. Output Voltage Amplitude (V_{OUTPP}) versus Input Clock Frequency (f_{in}) and Temperature (@ $V_{CC} = 3.3\text{ V}$)

NB4N855S

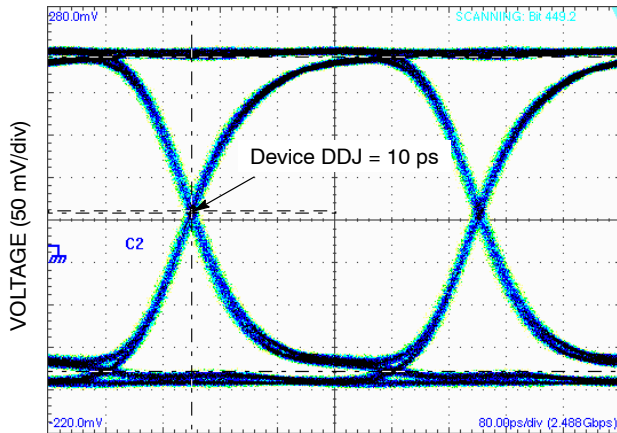


TIME (322 ps/div)

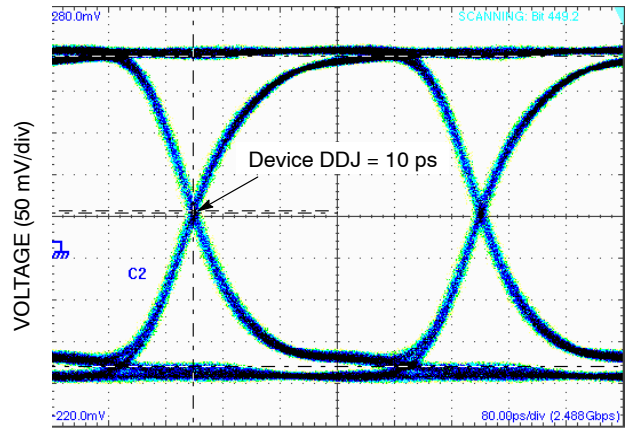


TIME (322 ps/div)

Figure 4. Typical Output Waveform at 1.5 Gb/s with $2^{23}-1$
 ($V_{INPP} = 100$ mV (left) & $V_{INPP} = 400$ mV (right), Input Signal DDJ = 24 ps)



TIME (80 ps/div)



TIME (80 ps/div)

Figure 5. Typical Output Waveform at 2.488 Gb/s with $2^{23}-1$
 ($V_{INPP} = 100$ mV (left) & $V_{INPP} = 400$ mV (right), Input Signal DDJ = 30 ps)

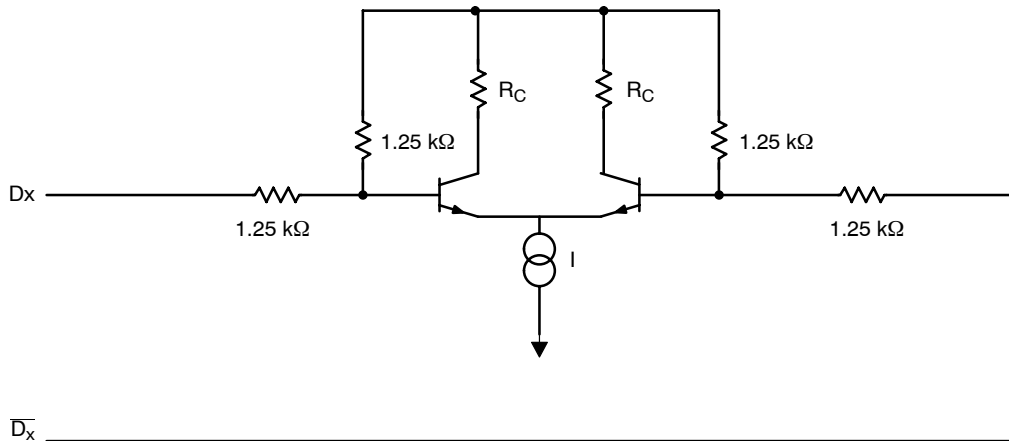


Figure 6. Input Structure

NB4N855S

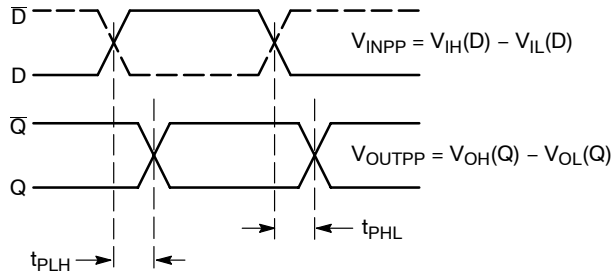


Figure 7. AC Reference Measurement

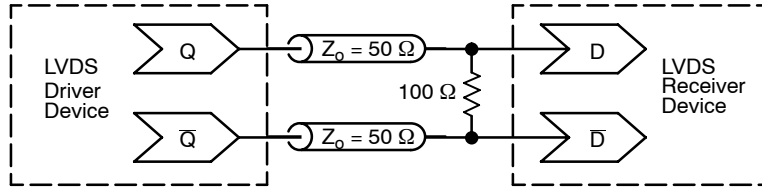


Figure 8. Typical LVDS Termination for Output Driver and Device Evaluation

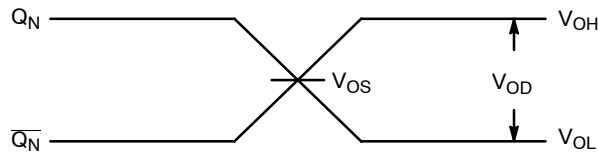


Figure 9. LVDS Output

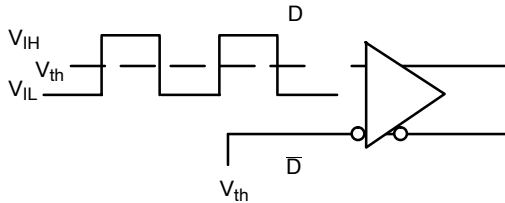


Figure 10. Differential Input Driven Single-Ended

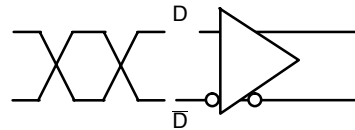


Figure 11. Differential Inputs Driven Differentially

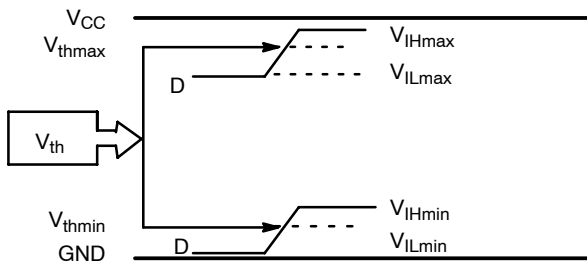


Figure 12. V_{th} Diagram

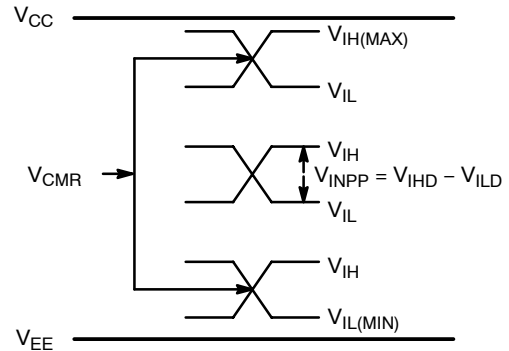


Figure 13. V_{CMR} Diagram

NB4N855S

ORDERING INFORMATION

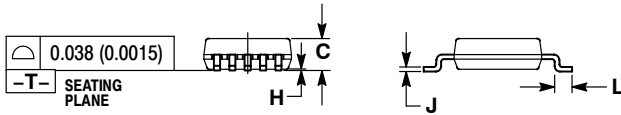
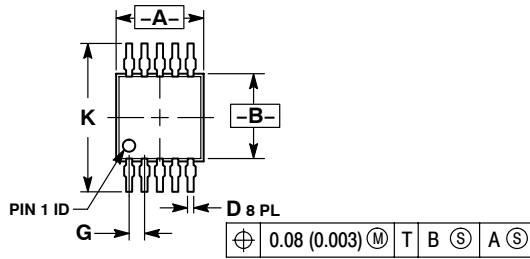
Device	Package	Shipping†
NB4N855SMR4	Micro-10	1000 / Tape & Reel
NB4N855SMR4G	Micro-10 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

NB4N855S

PACKAGE DIMENSIONS

Micro-10
CASE 846B-03
ISSUE D

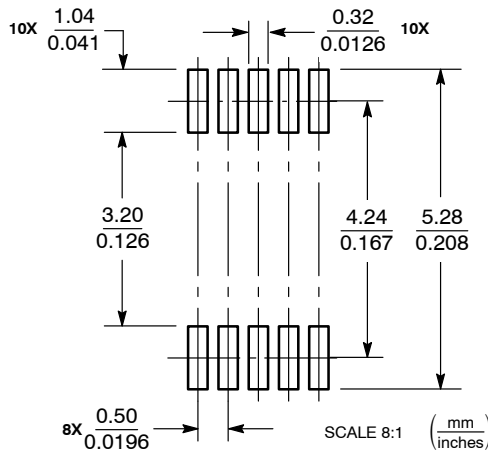


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION "B" DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. 846B-01 OBSOLETE. NEW STANDARD 846B-02

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.95	1.10	0.037	0.043
D	0.20	0.30	0.008	0.012
G	0.50 BSC		0.020 BSC	
H	0.05	0.15	0.002	0.006
J	0.10	0.21	0.004	0.008
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

AnyLevel is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.